Ordering number:EN2263A

PNP/NPN Epitaxial Planar Silicon Transistors

2SB1267/2SD1903

30V/8A High-Current Switching Applications

Applications

· Suitable for relay drivers, high-speed inverters, converters and other general high-current switching.

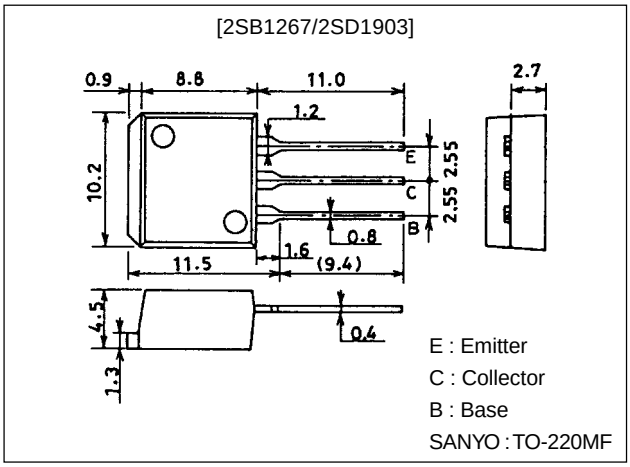
Features

· Suitable for sets whose height is restricted.
· Low collector to emitter saturation voltage : V_{CE}(sat)=–0.5V (PNP), 0.4V (NPN) max.
· Large current capacity.

Package Dimensions

unit:mm

2049B



( ) : 2SB1267

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)60	V
Collector-to-Emitter Voltage	V_{CEO}		(–)30	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)8	A
Collector Current (Pulse)	I_{CP}		(–)15	A
Collector Dissipation	P_C		1.65	W
		Tc=25˚C	30	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(–)40V, I_E=0			(–)0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(–)4V, I_C=0			(–)0.1	μA
DC Current Gain	$h_{FE}1$	V_{CE}=(–)2V, I_C=(–)1A	70*		280*	
	$h_{FE}2$	V_{CE}=(–)2V, I_C=(–)4A	30			
Gain-Bandwidth Product	f_T	V_{CE}=(–)5V, I_C=(–)1A		120		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(–)3A, I_B=(–)0.15A			0.4	V
					(–0.5)	V

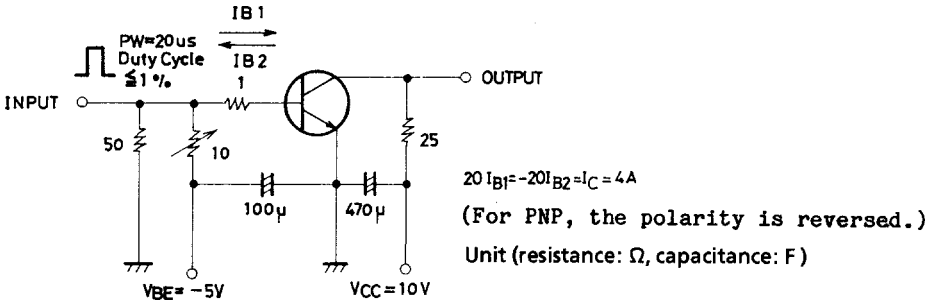
* : The 2SB1267/2SD1903 are classified by 1A h_{FE} as follows :

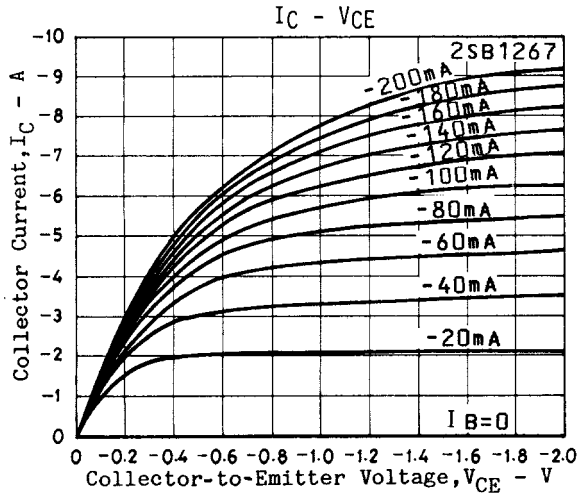
70	Q	140	100	R	200	140	S	280

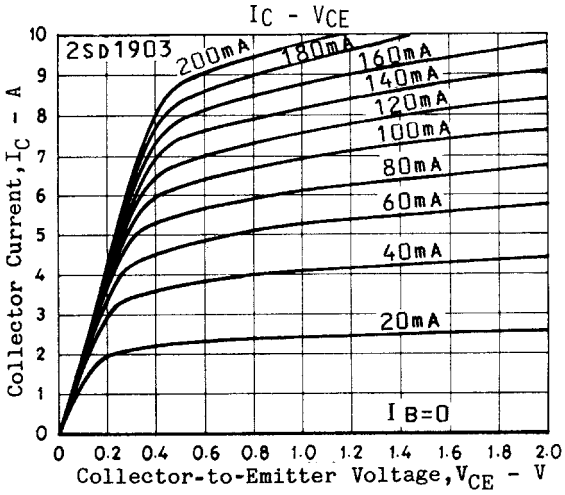
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

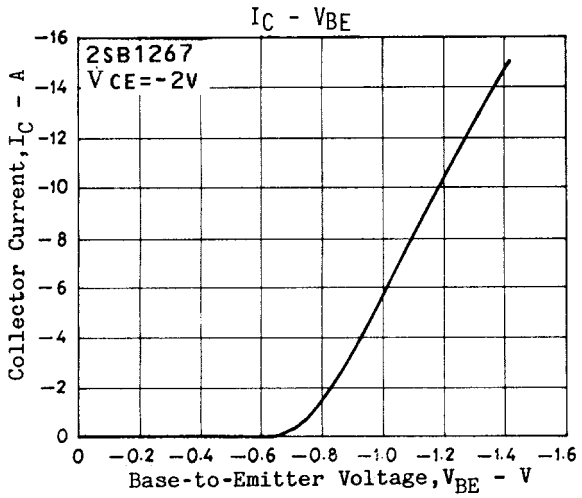
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(–)1mA, I_E=0	(–)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(–)1mA, R_{BE}=∞	(–)30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(–)1mA, I_C=0	(–)6			V
Turn-ON Time	t_{on}	See specified test circuit.		0.1		μs
Storage Time	t_{stg}	See specified test circuit.		(0.2)		μs
				0.5		μs
Fall Time	t_f	See specified test circuit.		0.03		μs

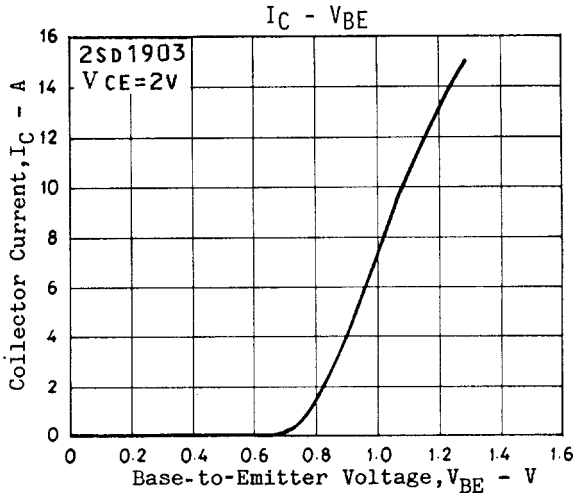
Switching Time Test Circuit

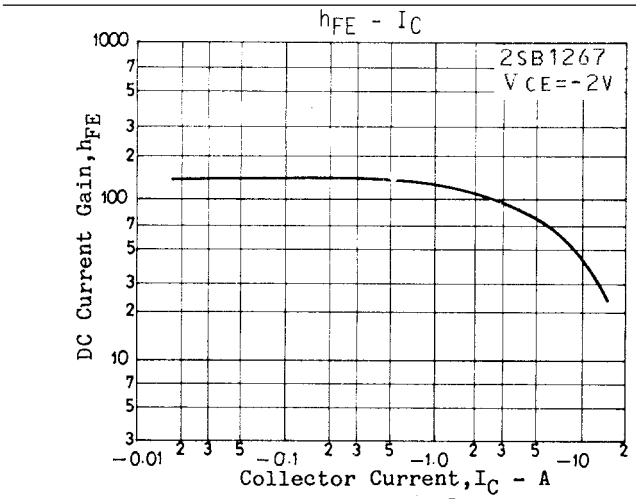


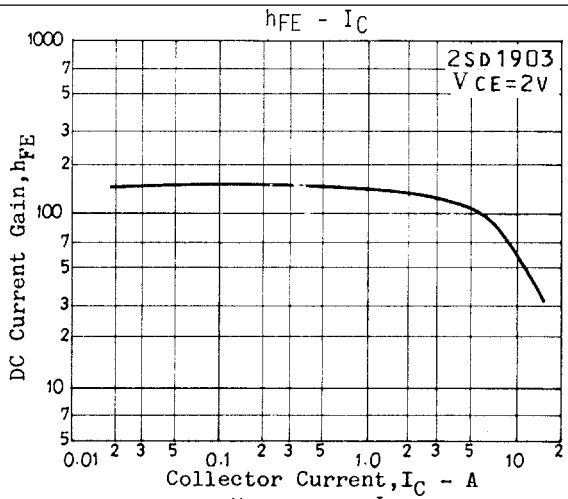


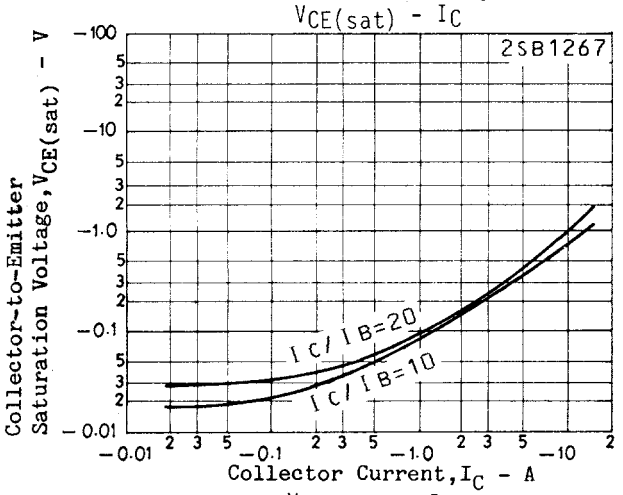


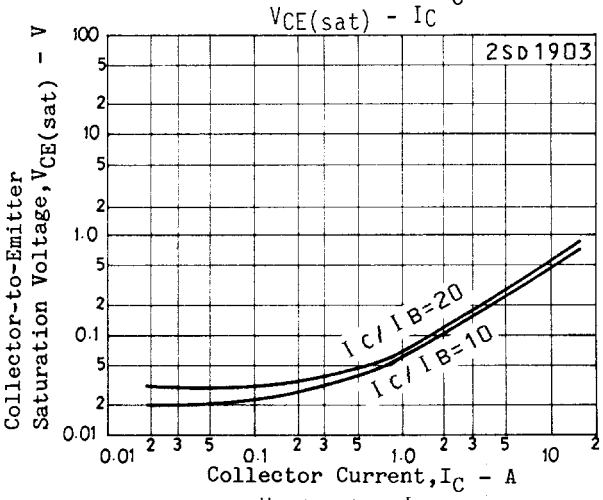


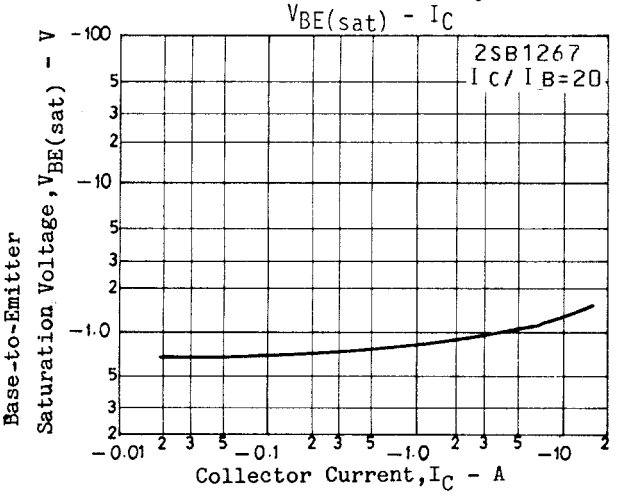


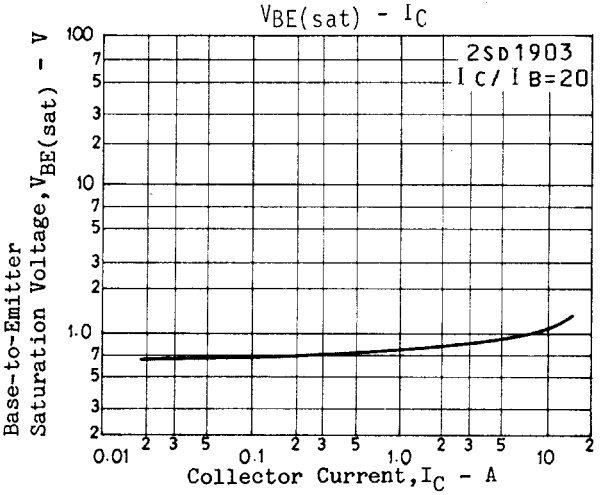

hFE - IC
2SB1267
VCE=-2V
DC Current Gain, hFE
Collector Current, IC - A

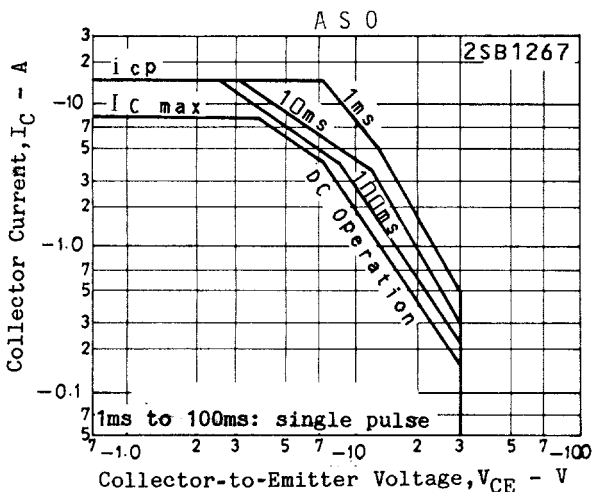

hFE - IC
2SD1903
VCE=2V
DC Current Gain, hFE
Collector Current, IC - A

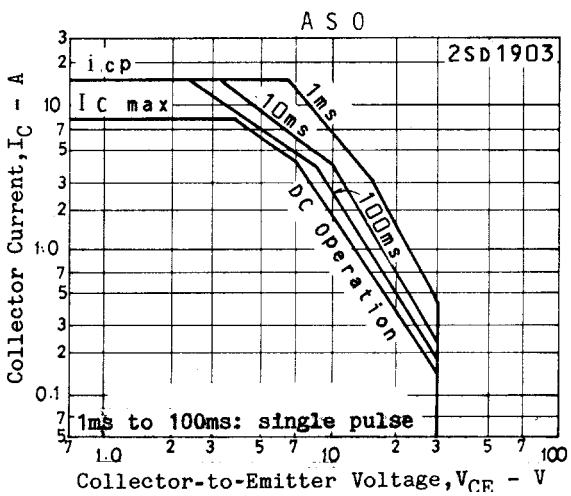

VCE(sat) - IC
2SB1267
IC/IB=20
IC/IB=10
Collector-to-Emitter Saturation Voltage, VCE(sat) - V
Collector Current, IC - A


VCE(sat) - IC
2SD1903
IC/IB=20
IC/IB=10
Collector-to-Emitter Saturation Voltage, VCE(sat) - V
Collector Current, IC - A


VBE(sat) - IC
2SB1267
IC/IB=20
Base-to-Emitter Saturation Voltage, VBE(sat) - V
Collector Current, IC - A


VBE(sat) - IC
2SD1903
IC/IB=20
Base-to-Emitter Saturation Voltage, VBE(sat) - V
Collector Current, IC - A


ASO
2SB1267
icp
IC max
1ms
10ms
100ms
DC operation
1ms to 100ms: single pulse
Collector Current, IC - A
Collector-to-Emitter Voltage, VCE - V


ASO
2SD1903
icp
IC max
1ms
10ms
100ms
DC operation
1ms to 100ms: single pulse
Collector Current, IC - A
Collector-to-Emitter Voltage, VCE - V